



Optical Sensors



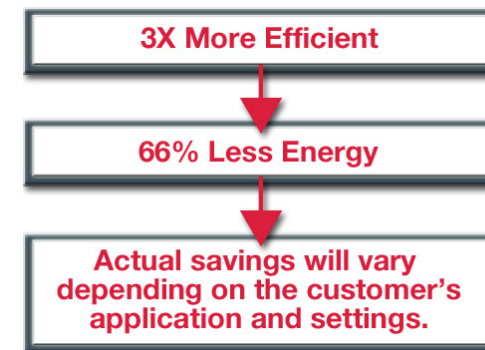
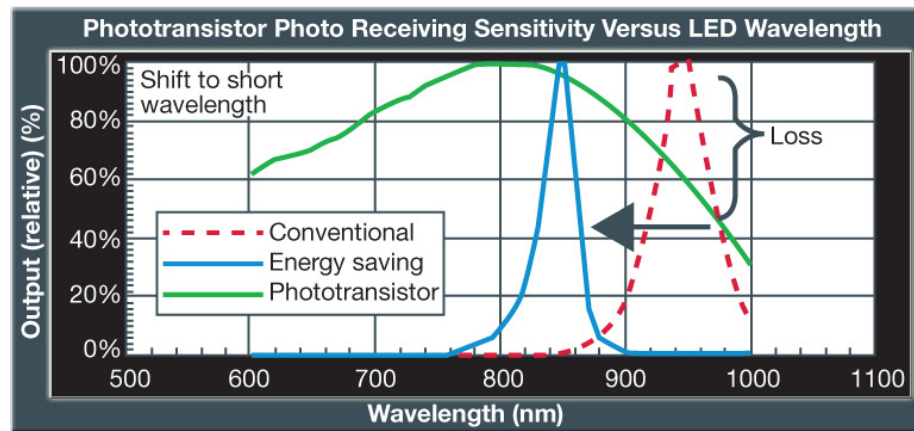
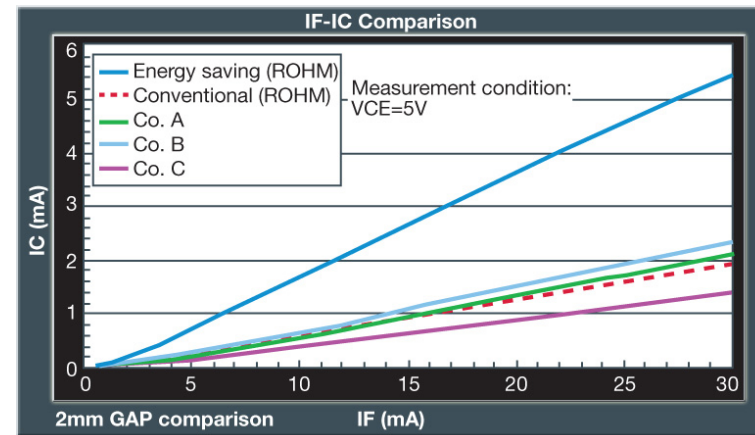
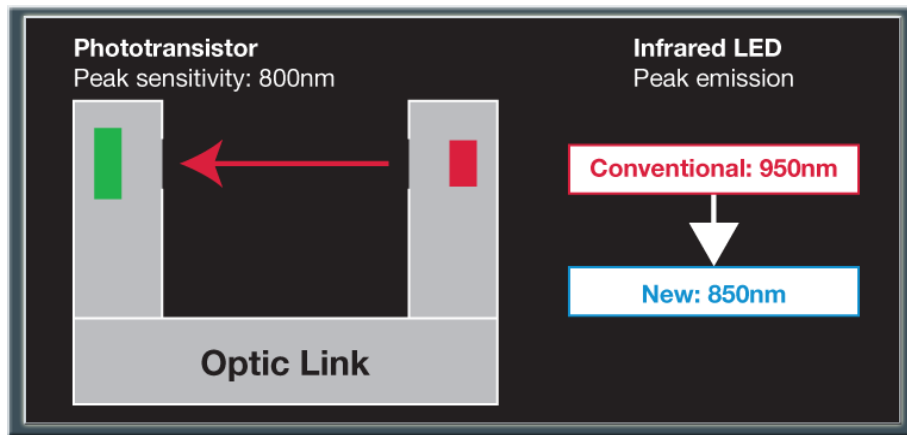
Sensor Markets



Applications	Examples
	Digital Cameras, Smart Phones/Pads Proximity Sensor; Image Rotation Sensor; Ambient Light Detection; Gesture Recognition
	Automotive Multi-switch; Air Conditioner; Power Seat; Steering Sensor; Infrared
	Factory Automation Motor Rotation Detection: Servo Motor; Power Mate
	Medical Motor Rotation Detection: Blood Pump; Syringe Pump
	Household Appliances Smoke Detection: Fire Detectors; Air Cleaners
	Security Infrared Lighting: Vein Authentication; Security Cameras
	Health Rotation & Position Detection: Massage Chair; Horse Riding Machine (Exercise Equipment)
	OA / Others Detection & Ejection: Shredder Paper Detection/Ejection; Sewing Machine Thread Detection
	ATM, Kiosk, Ticket Machine, Printer Positioning & Detection: Paper Positioning; Drawer & Cartridge Detection

Breakthrough Technology Achieves High Photo Conversion & Energy Savings in IR Optic Applications

This newly developed IR LED features light wavelength similar to the peak sensitivity wavelength of a phototransistor



Current consumption is decreased to 1/3 when used under the same characteristics versus current products

Low Profile IR LED for Sensors: SIM-030ST

Ideal for Proximity Sensors



LCD ON during standby LCD OFF while talking

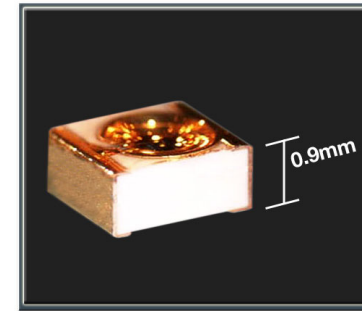
- Prevents malfunctions
- Saves battery power

For Touch-Free Sensors

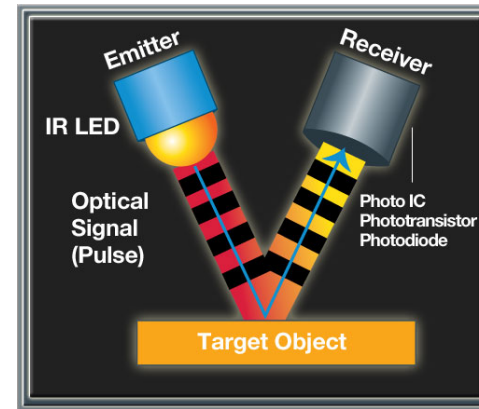


- Prevents smudges
- User interface

Thinnest IR LED: SIM-030ST



Proximity Sensor: Operating Principle



- Optical signals output from the emitter element (IR LED) are reflected off a target object and detected by the receiver element.
- Separates noise from other light sources (i.e. sunlight, fluorescent lamps).

Low Profile IR LED for Sensors: SIM-030ST

Applications

- Outdoor/high power devices



Mobile Phone



Proximity Sensor

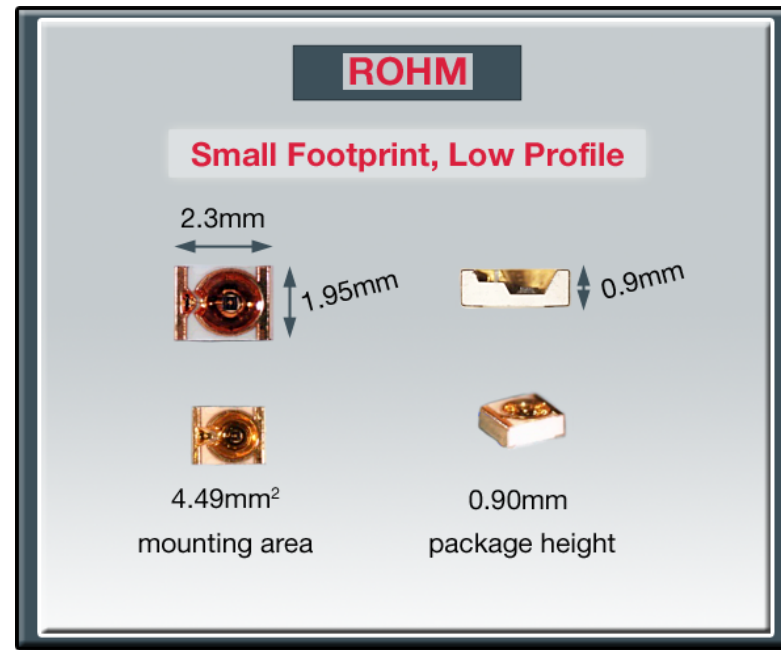


Single Lens Reflex Camera

Power saving with viewfinder display OFF

Package Comparison

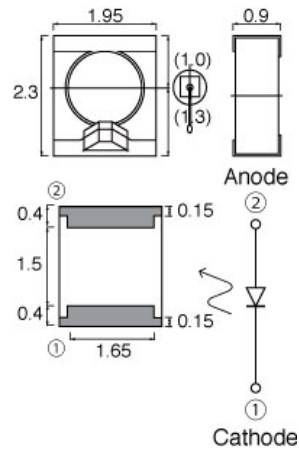
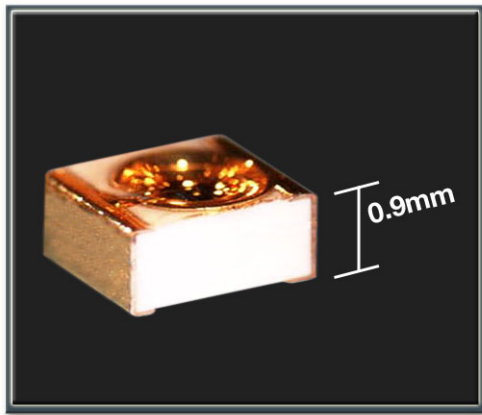
- 33% smaller mounting area than conventional models
- 42% thinner, narrow beam than conventional models
- MID structure (Improved beam phase matching & output power)



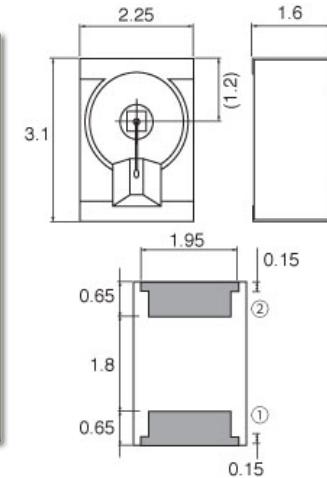
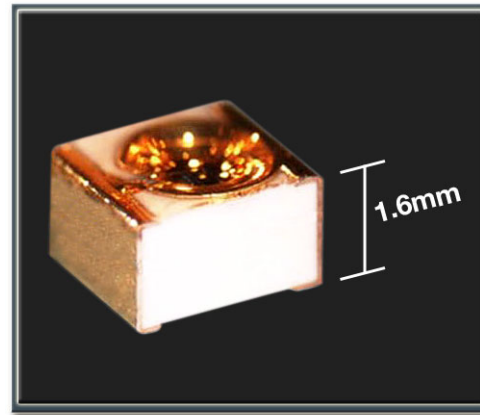
Low Profile High Power IR LEDs: SIM-030ST/031ST, SIM-040ST/041ST



SIM-030ST/031ST



SIM-040ST/ 041ST



Specifications

Part #	Forward Current (IF)	Power Dissipation (VR)	Operating Temperature (TOPR)	Min. Emitting Strength (IE)	Forward Voltage (VF)	Peak Emitting Wavelength (λP)	Half Viewing Angle (Φ½)	Response Time (tr. tf)
	mA	mW	°C	mW/sr	V	nm	deg	μs
SIM-030ST	100	180	-25 to 85	30	1.7	870	±20	0.1
SIM-031ST	100	180	-25 to 85	30	1.7	850	±20	0.1
SIM-040ST	100	180	-25 to 85	40	1.7	870	±20	0.1
SIM-041ST	100	180	-25 to 85	40	1.7	850	±20	0.1

Ultra-Compact Surface Mount Tilt Sensor (4-way Detection): RPI-1040



Broad Compatibility: Optically detects device orientation – ideal for image orientation and fall detection applications

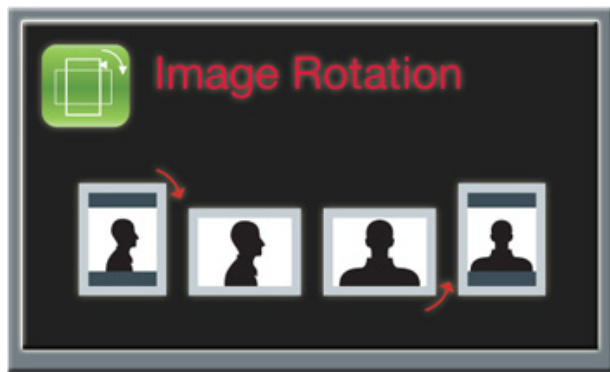


Image rotation
based on device position

Apps: Photo Display Devices
(Projectors, Photo Frames)



Simplifies preview
for image correction

Apps: Video Devices (Mobile
Phones, Digital Cameras)



Movement sensing – detects falls
and turns the power OFF

Apps: LCD TVs

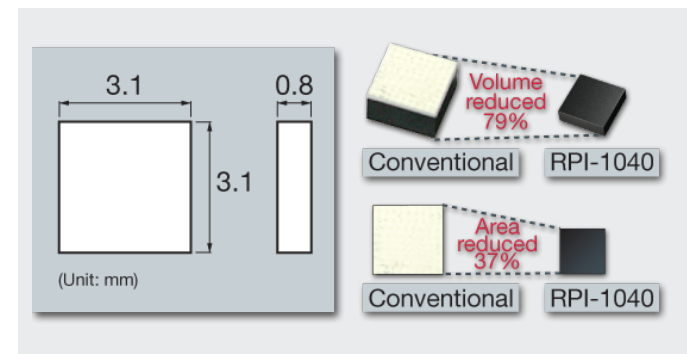
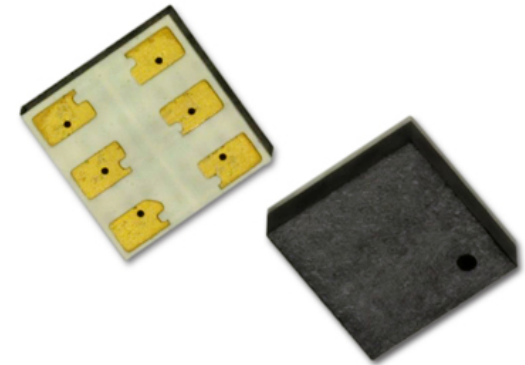
Ultra-Compact Surface Mount Tilt Sensor (4-way Detection): RPI-1040



Low profile package (0.8mm)

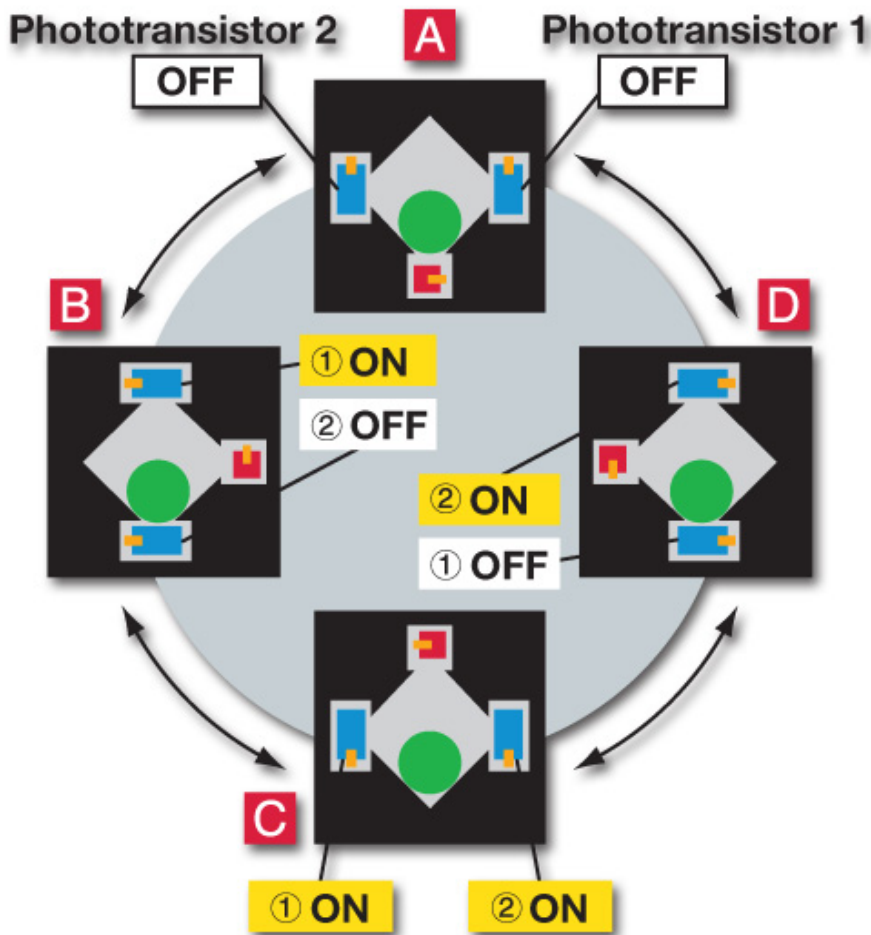
Features

- 4-way detection at 90° intervals using a shield IR diode and phototransistor
- Easy integration for instantaneous detection
- Simple design and optical method minimizes malfunctions and ensures high precision
- Utilization of a novel light shield results in no EMI noise emission



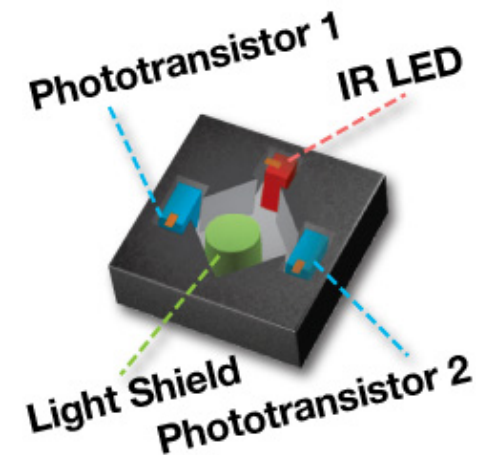
Tilt Sensor Operating Principle: RPI-1040

Silent Construction: During operation, the movement of the ball shield is suppressed.



Position	Phototransistor	
	①	②
A	OFF	OFF
B	ON	OFF
C	ON	ON
D	OFF	ON

Structural Diagram

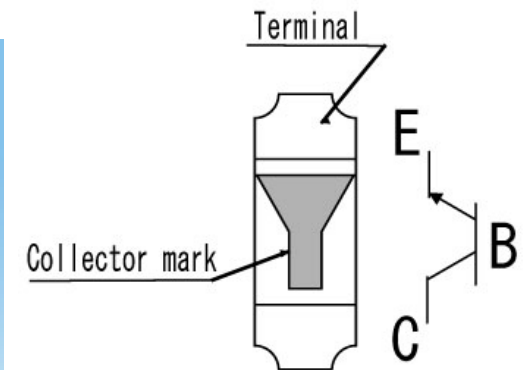
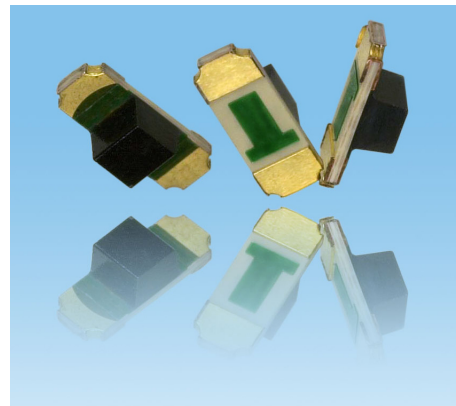


IR Phototransistor: SML-810TB

Molded lens, high accuracy, gain and collector current

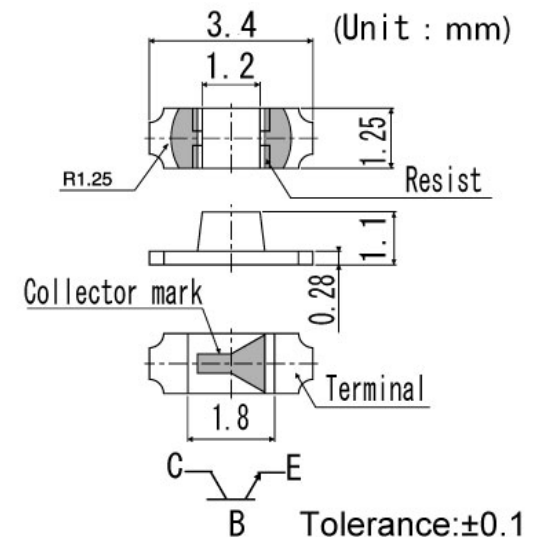
Absolute Maximum Ratings (Ta=25°C)

Rated Parameters	Standard Value
Collector-Emitter voltage $V_{CEO}(V)$	32
Emitter-Collector voltage $V_{ECO}(V)$	5
Collector current $I_C(mA)$	30
Power dissipation $P_C(mW)$	80
Operating temperature $T_{opr}(^{\circ}C)$	-30 to 85
Storage temperature $T_{stg}(^{\circ}C)$	-30 to 100



Electrical & Optical Characteristics (Ta=25°C)

Parameters		
Parameters	Value	Conditions
Photoelectric current-Min. $I_C(mA)$	2.3	$V_{CE}=5V, E=500Lx$
Dark current-Max. $I_{CEO}(\mu A)$	0.5	$V_{CE}=10V$ (Dark Box)
Peak sensitivity wavelength $\lambda P(nm)$	800	
Collector-Emitter saturation voltage-Max. $V_{CE(sat)}(V)$	10	μs
Response time t_r-t_f	-	

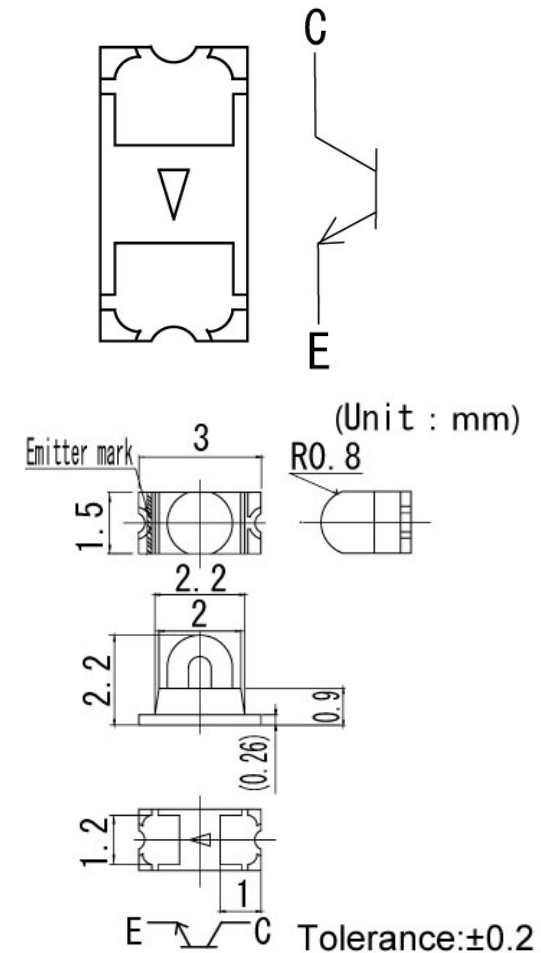


Top-view IR Phototransistor: SCM-014TB

Molded lens, high accuracy, gain and collector current

Absolute Maximum Ratings (Ta=25°C)

Rated Parameters	Standard Value
Collector-Emitter voltage $V_{CEO}(V)$	32
Emitter-Collector voltage $V_{ECO}(V)$	5
Collector current $I_C(mA)$	30
Power dissipation $P_C(mW)$	100
Operating temperature $T_{opr}(^{\circ}C)$	-30 to 85
Storage temperature $T_{stg}(^{\circ}C)$	-30 to 100



Electrical & Optical Characteristics (Ta=25°C)

Parameters		
Parameters	Value	Conditions
Photoelectric current-Min. $I_c(mA)$	0.5	$V_{CE}=5V, E=500Lx$
Dark current-Max. $I_{CEO}(\mu A)$	0.5	$V_{CE}=10V$ (Dark Box)
Peak sensitivity wavelength $\lambda P(nm)$	800	
Collector-Emitter saturation voltage-Max. $V_{CE(sat)}(V)$	0.4	$I_C=1mA, E=500Lx$
Response time $t_r \cdot t_f$	10	μs

Side-view IR Phototransistor/Sensor and Emitter: RPM-012PB, SIM-012SB

RPM-012PB - Ultra-compact, High Sensitivity Sensor

Features

- High sensitivity
- $\phi 2\text{mm}$ lens
- Ultra-compact surface mount package: 3mm x 3mm x 2mm
- Reflow-compatible

Applications

- Optical control equipment
- Receiver for sensors



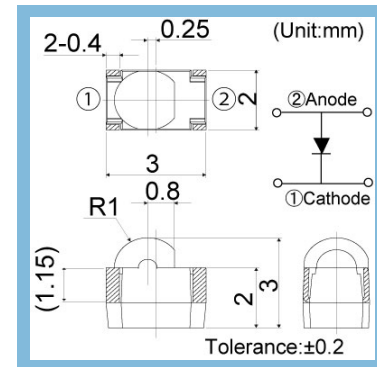
SIM-012SB - Ultra-compact, High Power Emitter

Features

- $\phi 2\text{mm}$ lens
- High power
- Ultra-compact surface mount package: 3mm x 3mm x 2mm
- Reflow-compatible

Applications

- Optical control equipment
- Light source for remote control devices



Side-view IR Phototransistor Sensor and Emitter: RPM-012PB, SIM-012SB



RPM-012PB Sensor

Absolute Maximum Ratings (Ta=25°C)

Rated Parameters	Standard Value
Collector-Emitter voltage $V_{CEO}(V)$	32
Emitter-Collector voltage $V_{ECO}(V)$	5
Collector current $I_C(mA)$	20
Power dissipation $P_C(mW)$	75
Operating temperature $T_{opr}(^{\circ}C)$	-30 to 85
Storage temperature $T_{stg}(^{\circ}C)$	-40 to 100

Electrical & Optical Characteristics (Ta=25°C)

Parameters		
Parameters	Value	Conditions
Photoelectric current-Min. $I_c(mA)$	0.56	$V_{CE}=5V, E=500Lx$
Dark current-Max. $I_{CEO}(\mu A)$	0.5	$V_{CE}=10V(\text{Dark Box})$
Peak sensitivity wavelength $\lambda P(nm)$	800	
Collector-Emitter saturation voltage-Max. $V_{CE}(sat)(V)$	0.4	$I_C=1mA, E=500Lx$
Response time t_r-t_f	10	$V_{CE}=5V, I_C=1mA, R_L=100\Omega$
Viewing angle $\theta_{1/2}(deg)$	± 12	

SIM-012SB Emitter

Absolute Maximum Ratings (Ta=25°C)

Rated Parameters	Standard Value
Forward current $I_F(mA)$	40
Reverse voltage $V_R(V)$	5
Power dissipation $P_D(mW)$	60
Pulse forward current $I_{FP}(A)$	0.5
Operating temperature $T_{opr}(^{\circ}C)$	-30 ~ +85
Storage temperature $T_{stg}(^{\circ}C)$	-40 ~ +100



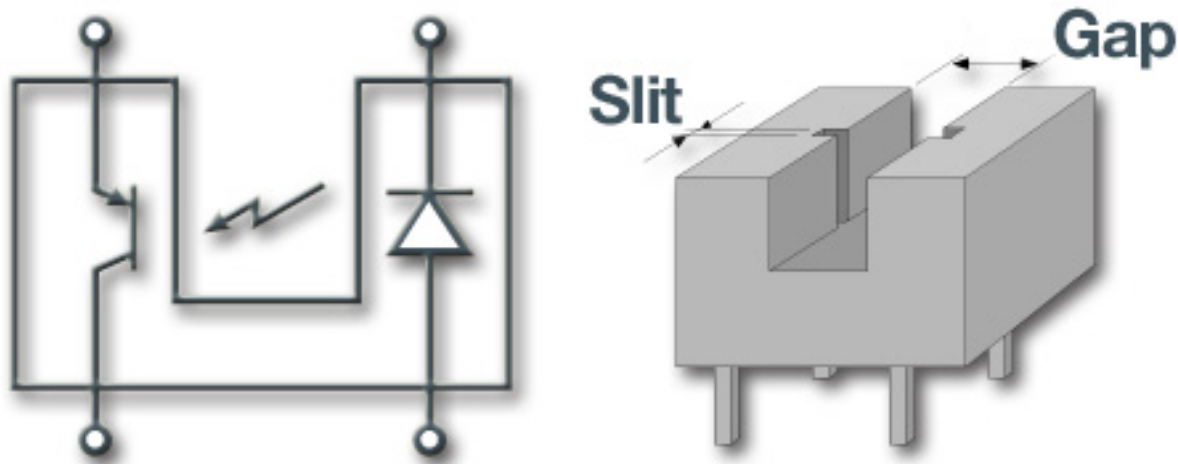
*Pulse width = 0.1msec, duty ratio 1%

Electrical & Optical Characteristics (Ta=25°C)

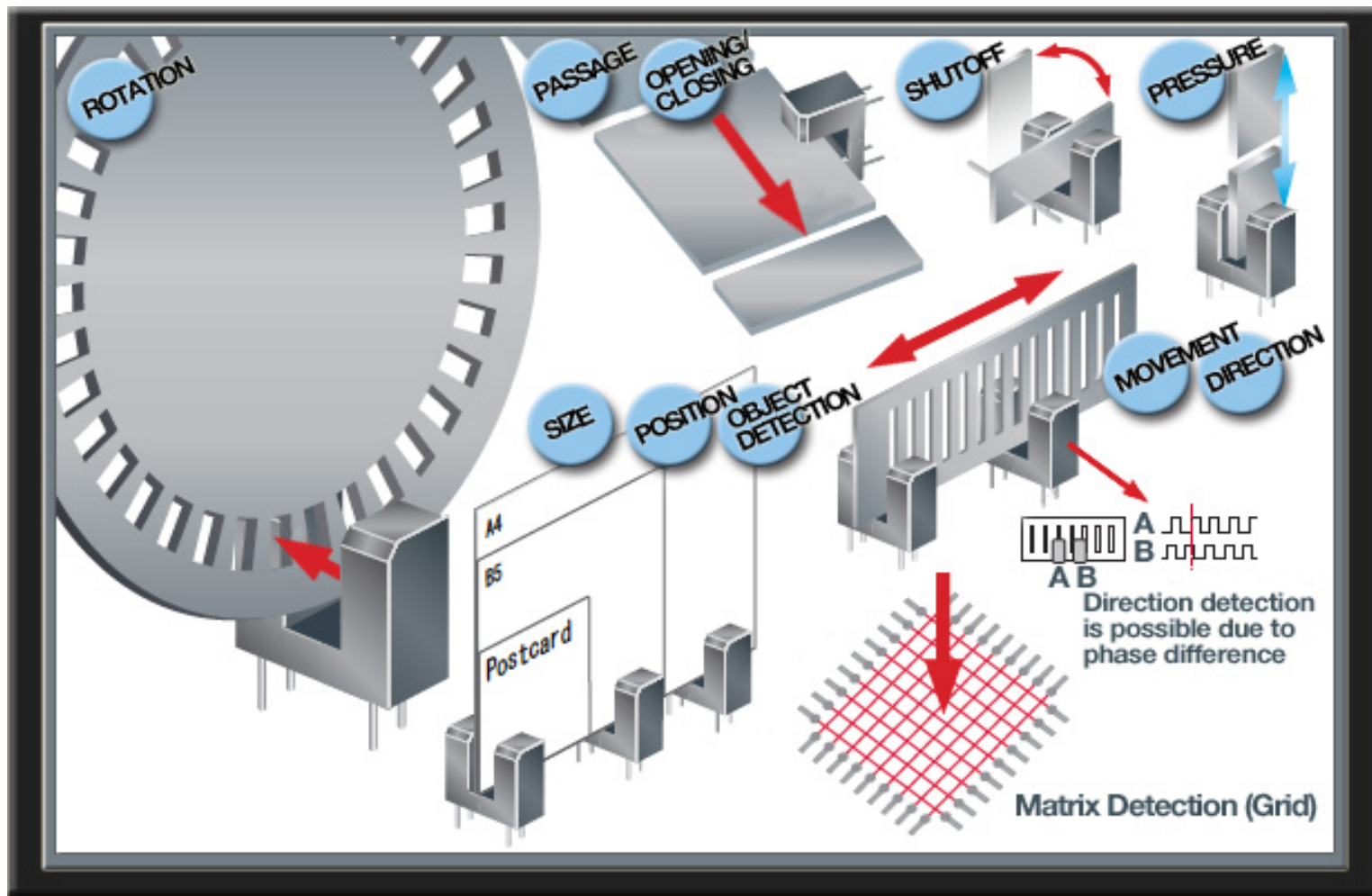
Parameters	Min.	Typ.	Max.	Conditions
Optical output $P_O(mW)$	-	3.5	-	$I_F=20mA$
Emitting strength $I_E(mW/sr)$	0.9	-	7.1	$I_F=20mA$
Forward voltage $V_F(V)$	-	1.2	1.5	$I_F=20mA$
Reverse current $I_R(\mu A)$	-	-	10	$V_R=3V$
Peak light emitting wavelength $\lambda P(nm)$	-	950	-	$I_F=20mA$
Spectral line half width $\Delta\lambda(nm)$	-	40	-	$I_F=20mA$
Half-viewing angle $\theta_{1/2}(deg)$	-	± 12	-	$I_F=20mA$
Response time $t_r-t_f(\mu s)$	-	1.0	-	$I_F=20mA$
Cut-off frequency $f_c(MHz)$	-	1.0	-	$I_F=20mA$

Photointerrupter (Transmission Type)

- A photointerrupter detects movement/positioning
- Photo sensor module comprised of an infrared diode and infrared sensor
- Detects the movement of objects passing through the gap between the emitter and receiver
- The photointerrupter slit influences the accuracy and timing position of detection points



Photointerrupter (Transmission Type)



Photointerrupter Lineup



SLIT	GAP	1mm	2mm	3mm	4mm	5mm
0.15mm		RPI-124			<p>photointerrupter slit gap</p>	
0.2mm		RPI-122	RPI-222			
		RPI-151 dual element → New	RPI-246			
0.3mm		RPI-125 RPI-129B RPI-130 horizontal aperture → New	RPI-0226	RPI-0227E	reflection type photointerrupter	
		RPI-0125 RPI-0126 RPI-0128 small → smaller → New	wide gap → surface mount	under development RPI-0352E under development surface mount		
0.4mm		RPI-121	RPI-221	RPI-352	focus distance 6mm	RPR-220C1 (940nm)
		RPI-131	RPI-243	RPI-303		RPR-220UC30 (630nm)
0.5mm			RPI-5100		RPI-392 RPI-441C1	RPI-2501 under development

Ultra-Compact Surface Mount Photointerrupters (Double Mold type): RPI-0128/128, RPI-0125



RPI-0128/128 Features

- Industry's smallest and lowest profile photointerrupter
- Miniaturized while maintaining a 1.2mm gap
- 28.6% smaller than the RPI-0126

Applications

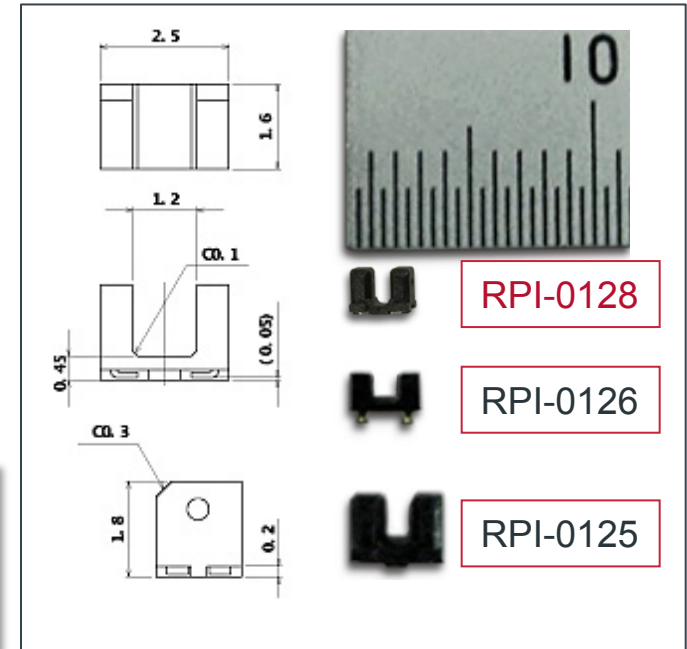
- Mobile phones
- Digital cameras
- Handheld devices



Electrical Characteristics

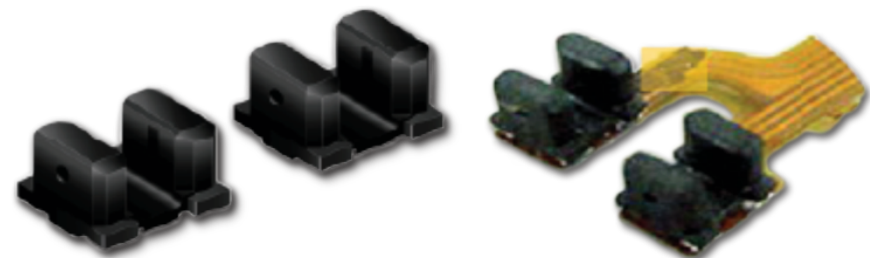
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	VF	1.2	1.35	1.5	V	IF=5mA
Collector Current	IC	1.0	-	5.0	mA	VCE=5V IF=5mA

Dimensions



RPI-0125 Features

- ROHM's smallest, low profile photointerrupter developed using original Double-Mold technology
- Contributes to thinner, smaller sets



Compatible with flex cables

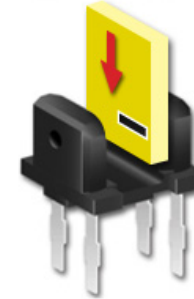
Ultra-Compact Surface Mount Wide Gap, Horizontal & Vertical Slits Photointerrupters (Double Mold Type): RPI-129B/125



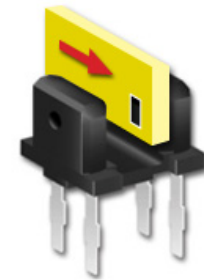
Features

- Wider gap (1.2mm)
- Narrow slit (0.3mm) high accuracy position detection
- Double-mold structure (a ROHM original)
- High reliability

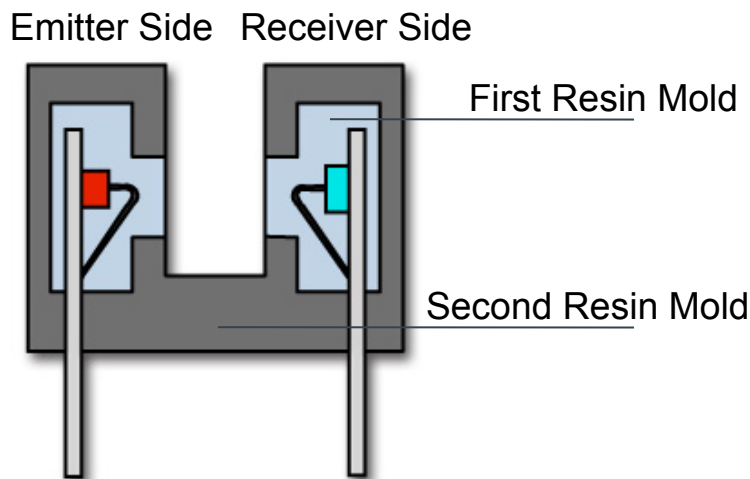
Horizontal Slit
RPI-129B



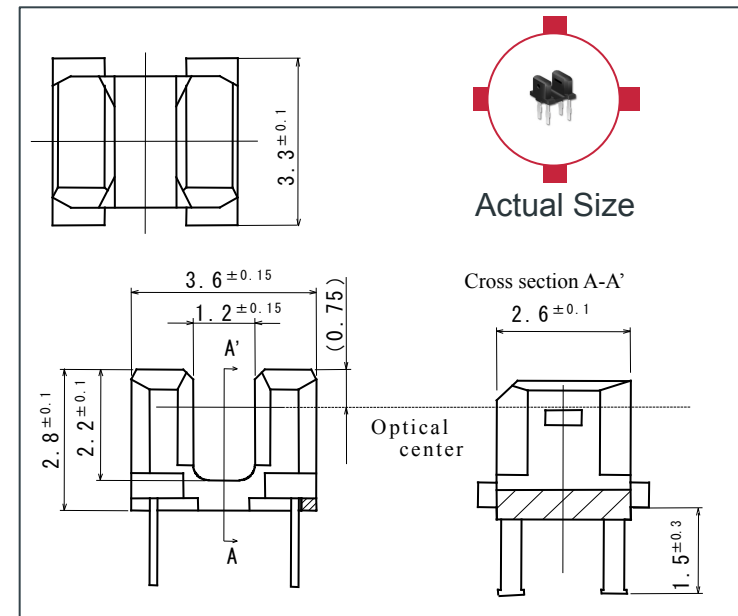
Vertical Gap Slit
RPI-125



Double-mold structure offers greater reliability & high accuracy.



Dimensions



2-Phase Output Photointerrupter: RPI-151

Key Feature

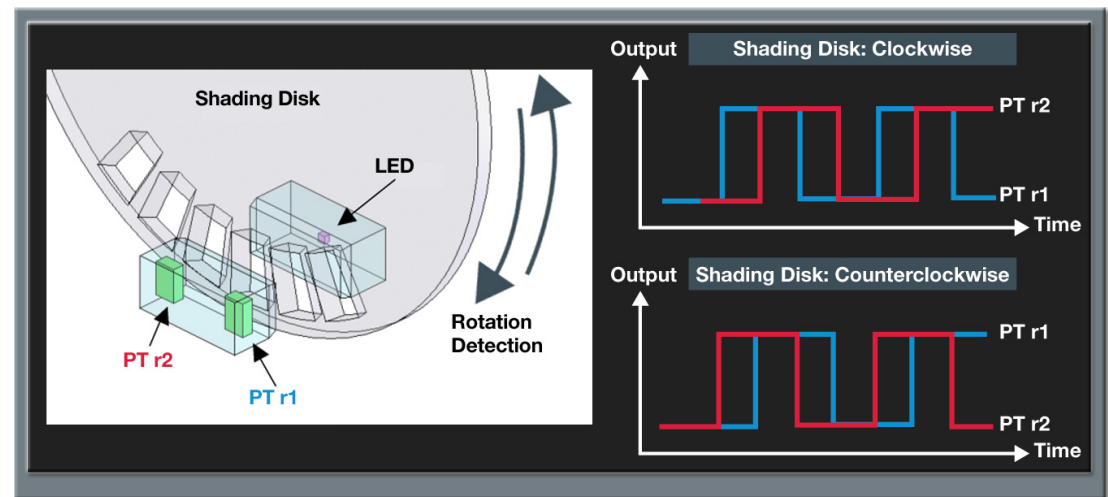
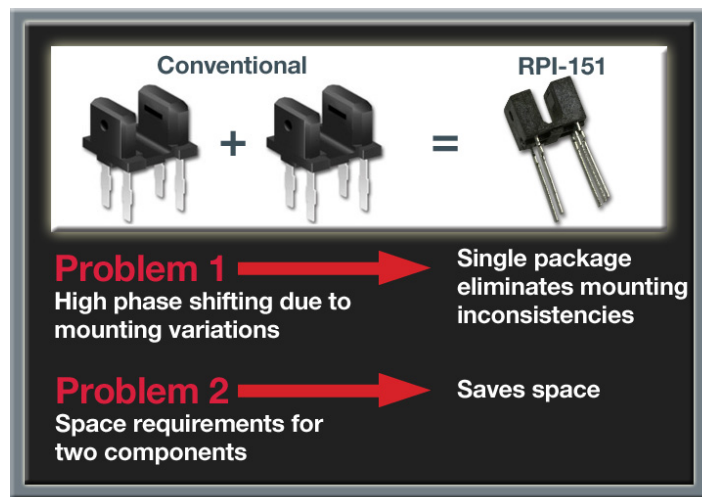
- Dual role - detects the spin speed and motor direction with greater accuracy than conventional two-device configurations

Applications

- Digital camera lens position sensing



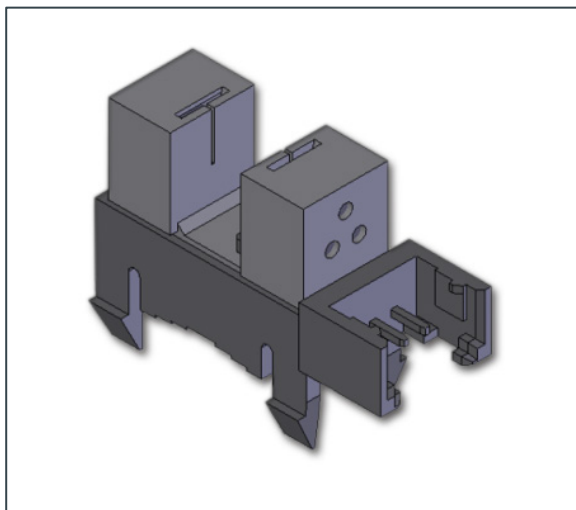
Operating Principle



Photointerrupter with Connector: RPI-2501

Features

- Dual mold structure with lens integrated into the primary mold
- Peak light wavelength: 850nm, high efficiency
- Panel clip mounting eliminates use of PCB
- CT mini connector
- Improved detection accuracy (0.4mm slit)



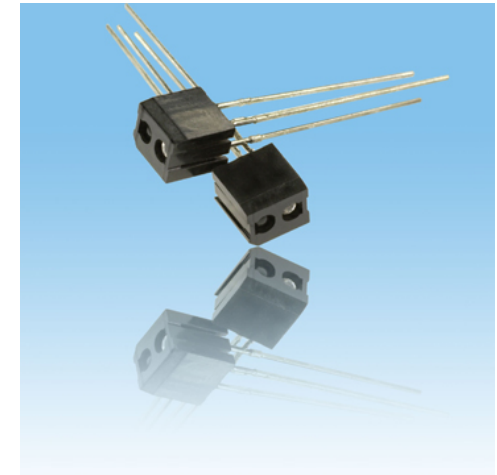
Reflective Type Photointerrupters: RPR-220C1

Features

- 940nm wavelength
- Plastic lens yields high sensitivity
- Built-in visible light filter minimizes stray light influences
- Light & compact
- Excellent reflection sensitivity (3-6mm)

Applications

- Printers, CD players, gaming machines



Emitter Part #	Forward Current (I _F)	Power Dissipation (P _d)	Operating Temperature (T _{OPR})	Forward Voltage (V _F)	Peak Emitting Wavelength (λ _P)	Switching Time
	mA	mW	°C	V	nm	μs
RPR-220C1	50	80	-25 to 85	1.34	940	1

Sensor Part #	Collector Current (I _c)	Power Dissipation (P _c)	Operating Temperature (T _{OPR})	Min. Photoelectric Current (I _c)	Collector-Emitter Voltage	Peak Sensitivity Wavelength (λ _P)	Max. Dark Current	Response Time (tr. tf)
	mA	mW	°C	mA	V	nm	μA	μs
RPR-220C1	30	80	-25 to 85	0.08	30	800	0.5	10

Reflective Type Photointerrupters: RPR-220UC30, RPR-220PC30N

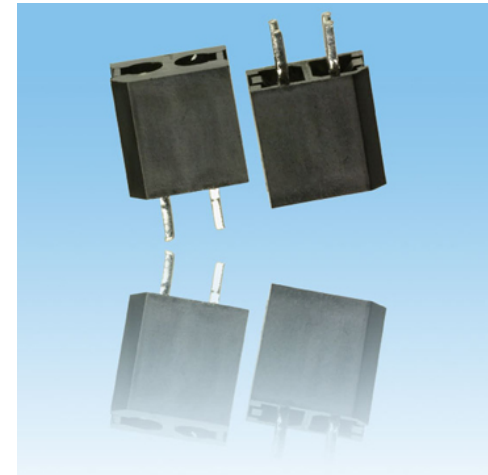


Features

- Plastic lens yields high sensitivity
- Built-in visible light filter minimizes stray light influence
- Light & compact
- RED and BLUE wavelength emitter

Applications

- Printers, medical, games



Emitter Part #	Forward Current (I _F)	Power Dissipation (P _d)	Operating Temperature (T _{OPR})	Forward Voltage (V _F)	Peak Emitting Wavelength (λ _P)	Switching Time
	mA	mW	°C	V	nm	μs
RPR-220UC30	30	80	-25 to 85	2	630	1
RPR-220PC30N	30	80	-25 to 85	2	470	1

Sensor Part #	Collector Current (I _c)	Power Dissipation (P _c)	Operating Temperature (T _{OPR})	Min. Photoelectric Current (I _c)	Collector-Emitter Voltage	Peak Sensitivity Wavelength (λ _P)	Max. Dark Current	Response Time (tr. tf)
	mA	mW	°C	mA	V	nm	μA	μs
RPR-220UC30N	30	80	-25 to 85	0.08	30	800	10	10
RPR-220PC30N	30	80	-25 to 85	0.08	30	800	10	10

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